

Anomalous Valley Magnetic Moment of Graphene

Daqing Liu, Shengli Zhang, Erhu Zhang, Ning Ma, Huawei Chen

Department of Applied Physics, Non-equilibrium Condensed Matter and Quantum Engineering Laboratory,
Key Laboratory of Ministry of Education, Xi'an Jiaotong University, Xi'an, 710049, China

Abstract

Carrier interactions on graphene are studied. The study shows that besides the well known Coulomb repulsion between carriers, there also exist four-fermion interactions associated with U-process, one of which attracts carriers in different valleys. We then calculate the contributions to valley magnetic moment from vertex correction and from four-fermion corrections explicitly. The relative contributions are -18% and 3% respectively. At last we point out that we can mimic heavy quarkonium system by carrier interactions in graphene.

1 Introduction

Graphene [1], newly discovered two-dimensional crystals, has attracted more and more attentions of theorists and experimentalists [2–5]. In graphene, there is a typical valley degeneracy, corresponding to the presence of two different valleys in the band structure. However, as stated in the reference [6], such degeneracy makes it difficult to observe the intrinsic physics of a single valley in experiments [7, 8]. How to distinguish carriers in the two valleys is therefore always a topic attracting literatures [6, 9–11].

Ref. [9] pointed out that in close analogy with the spin degree, there is an intrinsic magnetic moment associated with the valley index, which was called as valley magnetic moment (VMM). At tree level the valley magnetic moment is about 30 times that of the usual spin magnetic moment, therefore, "valleytronics" provides a new and much more standard pathway to potential applications in a broad class of semiconductors as compared with the novel valley device in graphene nanoribbon [10]. However, since in graphene the effective coupling $\frac{e^2}{\epsilon\hbar v} \sim 1$, a question to be posed is to what extent the calculation in ref. [9] is valid.

To answer the question, we first study carrier interactions. The study shows that, in tight binding approximation, besides the well-known Coulomb repulsion between electrons, there are also four-fermion interactions associated with U-process. The four-fermion interactions are type dependent and more significant, one of them attracts carriers in different valleys. Armed with the understanding of the interactions, we point out that there are two corrections to VMM at one-loop level. One is the vertex correction and the other is the four-fermion correction. The vertex correction is similar to the anomalous magnetic moment of a particle in quantum elec-

trodynamic (QED) except that carrier interactions on graphene are not "Lorentz covariant". Therefore, such correction always appears even in a one-valley system. Meanwhile, the valley degree is similar to the flavor degree in particle physics or high-energy physics. To compute anomalous magnetic moment of a particle due to flavor degree, one should also consider the weak interaction, an interaction between flavor degree. Our Yakawa-like four-fermion interactions are similar to the lower-energy approximation of the weak interactions. In this way, the correction to VMM due to valley degree appears at one-loop level. In contrast, such correction can not occur in QED.

Our study shows that the total correction is about -15%. Furthermore, since the corrections are independent on the divergence of the loop calculations, VMM can be used to check the validity of the perturbational calculation.

2 Carrier interactions

Here we study carrier interactions. The study shows that besides the well known Coulomb repulsion, there are also four-fermion interactions between carriers at different valleys, which are not only short-range but also contacting ones.

For simplicity, we set $\hbar \equiv 1$ and $X(\mathbf{r} - \mathbf{r}_{A'})$ the normalized orbital p_z wave function of electron bound to atom A' , *i.e.* it satisfies $\int d\mathbf{r} X(\mathbf{r} - \mathbf{r}_{A'}) X(\mathbf{r} - \mathbf{r}_{A''}) = \delta_{A'A''}$ [12]. A-electron wave function $\psi_A(\mathbf{k})$ in position space is $\psi_A(\mathbf{k}) = \sqrt{\omega}/(2\pi) \sum_A e^{i\mathbf{k}\cdot\mathbf{r}_A} X(\mathbf{r} - \mathbf{r}_A)$, where $\omega = \sqrt{3}a^2/2$ is the area of the hexagonal cell. For B-electron the case is similar. We then have $\langle \psi_{A'_0}(\mathbf{k}') | \psi_{A_0}(\mathbf{k}) \rangle = \delta_{A_0A'_0} \delta(\mathbf{k} - \mathbf{k}')$, where $A_0, A'_0 = A$ or B .

To study carrier interactions, we consider

$$V(\mathbf{k}) = \frac{(2\pi)^4}{N\omega} \psi_{A'_2}^*(\mathbf{k}_2 + \mathbf{k}) \psi_{A_2}(\mathbf{k}_2) \hat{V} \psi_{A'_1}^*(\mathbf{k}_1 - \mathbf{k}) \psi_{A_1}(\mathbf{k}_1) \quad (1)$$

where A_1, A'_1, A_2, A'_2 equal to A or B . If we ignore interchange interactions, the main contribution to $X^*(\mathbf{r}' - \mathbf{r}_{A'_2}) X(\mathbf{r}' - \mathbf{r}_{A_2}) \hat{V} X^*(\mathbf{r} - \mathbf{r}_{A'_1}) X(\mathbf{r} - \mathbf{r}_{A_1})$ should be at vicinity $\mathbf{r}_{A'_1} = \mathbf{r}_{A_1}$, $\mathbf{r}_{A'_2} = \mathbf{r}_{A_2}$, $\mathbf{r}' \approx \mathbf{r}_{A_2}$ and $\mathbf{r} \approx \mathbf{r}_{A_1}$. We get

$$\begin{aligned} V(\mathbf{k}) &= \delta_{A_1 A'_1} \delta_{A_2 A'_2} \sum_{A_1 A_2} e^{i\mathbf{k}(\mathbf{r}_{A_1} - \mathbf{r}_{A_2})} \frac{\omega e^2}{N|\mathbf{r}_{A_1} - \mathbf{r}_{A_2}|} \quad (2) \\ &= \delta_{A_1 A'_1} \delta_{A_2 A'_2} \sum_{A_2} e^{i\mathbf{k}(\mathbf{r}_{A_1} - \mathbf{r}_{A_2})} \frac{\omega e^2}{|\mathbf{r}_{A_1} - \mathbf{r}_{A_2}|}, \end{aligned}$$

where we have fixed A_1 in the last step. We shall ignore the two delta functions thereafter.

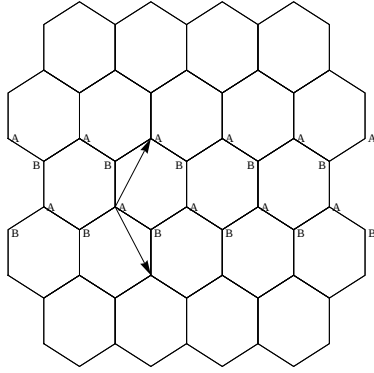


Figure 1: Graphene hexagonal lattice constructed as a superposition of two triangular lattices A and B, with bases vectors $\mathbf{a}_1 = a(\frac{1}{2}, \frac{\sqrt{3}}{2})$ and $\mathbf{a}_2 = a(\frac{1}{2}, -\frac{\sqrt{3}}{2})$, where lattice constant $a = |\mathbf{a}_1| = |\mathbf{a}_2|$. The reciprocal lattice vectors are $\mathbf{b}_1 = \frac{2\pi}{a}(1, \frac{1}{\sqrt{3}})$ and $\mathbf{b}_2 = \frac{2\pi}{a}(1, -\frac{1}{\sqrt{3}})$ respectively.

Without loss of generality, we set $A_1 = A$. To compute interactions between carriers, we first mark coordinates of A and B with two integers n_1 and n_2 . From Fig.1, the coordinate of one atom A is set as $(0,0)$. Then, for infinitely large graphene, coordinates of atom A are depicted as $(n_1/2, \sqrt{3}(n_1 - 2n_2)/2)a$ and coordinates of atoms B $(n_1/2, \sqrt{3}(n_1 - 2n_2 + \frac{2}{3})/2)a$ respectively, where a is lattice constant and n_1, n_2 are arbitrary integers.

We put our focus on the interactions between electrons around $\pm \mathbf{K} = \pm(4\pi/3a, 0)$. We first study the case where there is no valley-valley transition during interactions. For this case, we suppose $|\mathbf{k}a| \ll 1$. In Eq. (2) the function in the summation is a slow-moving function, therefore, the summation can be replaced by an integral,

$$V_c(\mathbf{k}) \approx e^2 \int d\mathbf{r} \frac{e^{i\mathbf{k} \cdot \mathbf{r}}}{|\mathbf{r}|} = \frac{2\pi e^2}{\varepsilon k}. \quad (3a)$$

where we have inserted the effective permittivity ε in the last equation to include screening effect. We thus obtain the well known Coulomb interaction. The type of A_2 does not influence the results, that is, the Coulomb repulsion works both for carriers in the same valley and for carriers in the different valleys.

Besides the well known Coulomb interactions, there are other interactions which is related to valley-valley transition. Such interactions correspond to a U-process and therefore $\mathbf{k} \approx \pm(4\pi/3a, 0)$. To deal with such case, we substitute $\mathbf{k} + (\frac{4\pi}{3a}, 0)$ for $\mathbf{k}$ in Eq.

We first consider A-B interactions, that is, $A_2 = B$ in Eq. (2). We get then

$$\begin{aligned} V_d(\mathbf{k}) &\approx e^2 \sum_{n_1 \neq 0} \frac{a}{2} e^{-ik_x \frac{n_1 a}{2} - i \frac{2\pi}{3} n_1} 2K_0(|k_y \frac{n_1 a}{2}|) \\ &+ e^2 \frac{a}{2} \sum_{n_2} \frac{e^{ik_y \sqrt{3}a(n_2 - \frac{1}{3})}}{|n_2 - \frac{1}{3}|} \approx 0.1e^2 a. \end{aligned} \quad (3b)$$

Compared to the long-wavelength result in Eq. (3a), the valley-valley interaction suffers a coefficient suppression due to the large momentum transfer. However, since such valley-valley interactions are short-range, it is not needed to consider screening effect. We therefore does not insert the effective permittivity ε in the above equation.

Whereas when $A_2 = A$, one should subtract the contribution from self interactions, which corresponds to $(n_1, n_2) = (0, 0)$ in Eq. (2). The result is then

$$V_s(\mathbf{k}) \approx -1.55e^2 a. \quad (3c)$$

Here, the large negative coefficient -1.55 is due to the subtraction.

Since Coulomb interaction is long-range, it does not depend on the distributing detail of the adjoint electrons. Thus, as shown in Eq. (3a), such interaction is type-independent. However, the four-fermion form of the U-process implies that such interactions are short-range and they therefore depend on the distributing detail. Therefore, as shown by (3b) and (3c), such interactions are type-dependent. Reference [13, 14] also proposed four-fermion interactions from different aspects. In Ref. [13] the authors add a near-neighbor interaction term and then, when they carry out momentum integral in the first Brillouin zone, they adhere the short-range interaction with the usual Coulomb interaction at $|\mathbf{k}| = \frac{1}{2} \frac{\pi}{\sqrt{3}a}$, where $\mathbf{k}$ is the transfer momentum. In contrast, in our approach, there is no artificial adhering and the interactions due to the valley transition are shown explicitly. Furthermore, the results obtained by our approach are suitable to take the quantum field theory calculations.

We emphasize that, besides the vertex correction, V_s also contributes to VMM. Furthermore, since

$V_s < 0$, it takes attracting force between electrons in different valleys. The interaction may play crucial role in superconduction phenomena^[15]. Therefore, V_s deserves further research.

3 The formal development of Lagrangian

We first define two two-component spinors φ and χ as follows: $\varphi = \begin{pmatrix} a_{\mathbf{K}(\mathbf{p})} \\ b_{\mathbf{K}(\mathbf{p})} \end{pmatrix}$ and $\chi = \begin{pmatrix} -ib_{-\mathbf{K}(\mathbf{p})} \\ ia_{-\mathbf{K}(\mathbf{p})} \end{pmatrix}$, where $\pm\mathbf{K}$ are two valleys. To describe the graphene dynamics in field theory language, we read the Lagrangian,

$$\begin{aligned} \mathcal{L}_0 = & \bar{\varphi}(i\gamma^0\partial_t + iv_r\gamma \cdot \nabla - m)\varphi - e\bar{\varphi}(\gamma^0 A^0 - \beta\gamma \cdot \mathbf{A})\varphi \\ & + \bar{\chi}(i\gamma^0\partial_t + iv_r\gamma \cdot \nabla + m)\chi - e\bar{\chi}(\gamma^0 A^0 - \beta\gamma \cdot \mathbf{A})\chi \\ & - \frac{\lambda_1}{2}\bar{\varphi}\gamma^1\chi\bar{\chi}\gamma_1\varphi - \frac{\lambda_2}{2}\bar{\varphi}\gamma^2\chi\bar{\chi}\gamma_2\varphi, \end{aligned}$$

where $\beta = v/c$, v is the Fermi velocity of carriers, c is the effective light velocity in graphene, $\lambda_1 = -(V_s - V_d)/2$ and $\lambda_2 = -(V_s + V_d)/2$. We also set three gamma matrices as $\gamma^0 = \gamma_0 = \sigma_3 = \begin{pmatrix} 1 & 0 \\ 0 & -1 \end{pmatrix}$, $\gamma^1 = g^{11}\gamma_1 = -\gamma_1 = \gamma^0\sigma_1 = \begin{pmatrix} 0 & 1 \\ -1 & 0 \end{pmatrix}$ and $\gamma^2 = g^{22}\gamma_2 = -\gamma_2 = \gamma^0\sigma_2 = \begin{pmatrix} 0 & -i \\ -i & 0 \end{pmatrix}$, where σ_i 's are three Pauli matrices and metric matrix $g^{\mu\nu} = \text{diag}\{1, -1, -1\}$. Since four-fermion interactions in Eqs. (3b) and (3c) are contacting ones, it is not necessary to introduce corresponding gauge field. In the above equation the energy gap m can be used to improve the use of graphene in making transistors and is therefore the one of the hot spots of literatures. In Ref. [16], the authors investigate the energy gap of graphene on a substrate BN, which is generated by the breaking of the A-B sublattice symmetry. However, such energy gap has not been observed up to now. In Ref. [17] the authors report that single layer graphene on SiC has a gap of 0.26eV, but the result is under debate [18, 19].

Utilizing the definitions of γ matrix and boost generators corresponding to "Lorentz" transformation we find positive solution and negative solution for φ field (or negative solution and positive solution for χ field) as $u(\mathbf{p}) = (\sqrt{p^0 + m}, v(p^1 + ip^2)/\sqrt{p^0 + m})^T$ and $v(\mathbf{p}) = (v(p^1 - ip^2)/\sqrt{p^0 + m}, \sqrt{p^0 + m})^T$ respectively. They meet $\not{p}u(p) = mu(p)$, $\bar{v}(p')\not{p}' = -\bar{v}(p')m$, where $\not{p} = \gamma_\mu \tilde{p}^\mu$ and $\tilde{p} = (p^0, v\mathbf{p})$.

However, the Lagrangian in Eq. (4) is a bare one and it needs renormalization to match the observable quantities^[20]. Having set $\varphi = Z_2^{1/2}\varphi_r$, $\chi = Z_2^{1/2}\chi_r$ and $A = Z_3^{1/2}A_r$, where φ_r , χ_r and A_r are renormalized quantities, we split each term of the Lagrangian

into two pieces as follows:

$$\begin{aligned} \mathcal{L} = & \bar{\varphi}_r(i\gamma^0\partial_t + iv_r\gamma \cdot \nabla - m_r)\varphi_r \\ & - e_r\bar{\varphi}_r(\gamma^0 A_r^0 - \beta_r\gamma \cdot \mathbf{A}_r)\varphi_r \\ & + \bar{\chi}_r(i\gamma^0\partial_t + iv_r\gamma \cdot \nabla + m_r)\chi_r \\ & - e_r\bar{\chi}_r(\gamma^0 A_r^0 - \beta_r\gamma \cdot \mathbf{A}_r)\chi_r \\ & - \frac{\lambda_{1r}}{2}\bar{\varphi}_r\gamma^1\chi_r\bar{\chi}_r\gamma_1\varphi_r - \frac{\lambda_{2r}}{2}\bar{\varphi}_r\gamma^2\chi_r\bar{\chi}_r\gamma_2\varphi_r \\ & + \bar{\varphi}_r(i\delta_2\gamma^0\partial_t + i\delta_v v_r\gamma \cdot \nabla - \delta_m)\varphi_r \\ & + \bar{\chi}_r(i\delta_2\gamma^0\partial_t + i\delta_v v_r\gamma \cdot \nabla + \delta_m)\chi_r \\ & - e_r\bar{\varphi}_r(\delta_1\gamma^0 A_r^0 - \beta_r\delta_c\gamma \cdot \mathbf{A}_r)\varphi_r \\ & - e_r\bar{\chi}_r(\delta_1\gamma^0 A_r^0 - \beta_r\delta_c\gamma \cdot \mathbf{A}_r)\chi_r \\ & - \frac{\delta_{1\lambda}}{2}\bar{\varphi}_r\gamma^1\chi_r\bar{\chi}_r\gamma_1\varphi_r - \frac{\delta_{2\lambda}}{2}\bar{\varphi}_r\gamma^2\chi_r\bar{\chi}_r\gamma_2\varphi_r \end{aligned} \quad (5)$$

where counterterm coefficients $\delta_2 = Z_2 - 1$, $\delta_m = Z_2 m - m_r$, $\delta_v = Z_2 v/v_r - 1$, $\delta_1 = Z_2 Z_3^{1/2} e/e_r - 1 \equiv Z_1 \chi - 1$, $\delta_c = Z_1 \beta/\beta_r - 1$, $\delta_{1\lambda} = Z_2^2 \lambda_1 - \lambda_{1r}$ and $\delta_{2\lambda} = Z_2^2 \lambda_2 - \lambda_{2r}$ are determined by renormalized conditions.

Since all the quantities in the following are renormalized ones, all the subscripts r will be dropped out.

4 Calculation of VMM

To compute the VMM we first show Feynman rules in Fig. 2 (a)-(e). The contribution to VMM up to e^2 is depicted by Fig.2(g), two diagrams in Fig.2(h), which is denoted by $\delta\Gamma_l^\mu$, $l = 1, 2$, Fig.2(i), which is denoted by Γ^μ , and the counterterm, Fig.2(f). The scattering amplitude of carrier under external gauge field is

$$i\mathcal{M} = -ie' \{ \bar{u}(p')(1 + \delta_1)\gamma^\mu u(p) + \Gamma^\mu + \sum_{l=1}^2 \delta\Gamma_l^\mu \} A_\mu^{cl}(\mathbf{q}), \quad (6)$$

where counterterm δ_1 plays a similar role as $Z_{int} - 1$ and $Z_{kin} - 1$ in Ref. [21], and $A_\mu^{cl}(\mathbf{q})$ is the Fourier transformation of the external field, p' and p are outgoing and incoming momentums of carrier respectively. Since we are working in lower energy limit, we ignore the renormalization of Fermi velocity and charge. We get

$$\begin{aligned} \delta\Gamma_l^\mu = & -i\lambda_l \int \frac{d^3k}{(2\pi)^3} \frac{\bar{u}(p')\gamma^l(\tilde{k} - m)\gamma^\mu(\tilde{k}' - m)\gamma_l u(p)}{[\tilde{k}^2 - m^2 + i\eta][\tilde{k}'^2 - m^2]} \\ \Gamma^\mu = & \frac{2\pi ie^2}{\varepsilon v^4} \int \frac{d^3k}{(2\pi)^3} \frac{u^\dagger(p')(\tilde{k}'' + m)\gamma^\mu(\tilde{k} + m)\gamma_0 u(p)}{[\tilde{k}''^2 - m^2 + i\eta][\tilde{k}^2 - m^2]} \mathbf{p} - \mathbf{k} \end{aligned} \quad (7)$$

respectively, where $q = p' - p$, $k'' = k + q$ and $k' = k - q$. In the above equation, we do not sum over the repeated index l and the terms proportional to $\beta^2 \sim 10^{-4}$ are neglected.

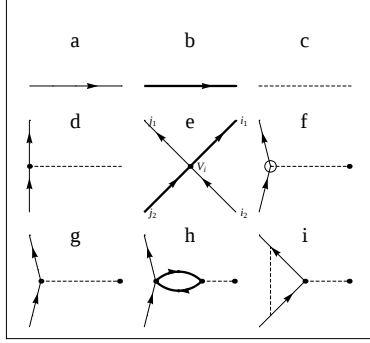


Figure 2: Feynman rule and Feynman diagram on graphene. a) Propagator of φ field with momentum p , $i\frac{\not{p}+m}{(\bar{p})^2-m^2+i\epsilon}$, where ϵ is infinitesimal positive. b) Propagator of χ field, $i\frac{\not{p}-m}{(\bar{p})^2-m^2+i\epsilon}$. c) Propagator of gauge field, $\frac{2\pi i}{\epsilon}\frac{g_{\mu\nu}}{p-i\epsilon}$. d) Interaction vertex between φ field and gauge field, $-ie'\gamma^\mu$, where $e' = e$ for $\mu = 0$ and $e' = \beta e$ for $\mu = 1, 2$. For χ field the interaction is similar. e) Two vertices of four-fermion interactions, $-i\lambda_1\gamma_{i_1i_2}^1\gamma_{1j_1j_2}^1$ and $-i\lambda_2\gamma_{i_1i_2}^2\gamma_{2j_1j_2}^2$. f) Counterterm vertex, $-ie'\delta_1\gamma^\mu$. Since we are only concerned about the correction to VMM up to order e^2 , the renormalization of fermion velocity is ignored. g) Tree level diagram contributing to VMM. h) Four-fermion corrections. i) Vertex correction.

Since the external field is time-independent, $q^0 = p'^0 - p^0 = 0$ in Eq. (7). If the electromagnetic field varies very slowly over a large region, Fourier components of the electromagnetic field will be concentrated about $\mathbf{q} = 0$. We can thus take nonrelativistic limit, $\mathbf{q} \rightarrow 0$, in $i\mathcal{M}$, which means $|\mathbf{p}|, |\mathbf{p}'|, |\mathbf{q}| \leq m/v$. Therefore, we have relations $-(\tilde{q})^2 = v^2\mathbf{q}^2 > 0$ and $\tilde{p}\tilde{p}' = (p^0)^2 - v^2\mathbf{p} \cdot \mathbf{p}' \approx m^2$.

To study the response to external magnetic field, we set time component of A_{cl} as zero, *i.e.* $A_{cl}(\mathbf{q}) = (0, \mathbf{A}(\mathbf{q}))$. We therefore only need to calculate the spatial part in $i\mathcal{M}$.

Since our theory violates the "Lorentz covariance", we should treat the result carefully. Furthermore, all the integrals in Eq. (7) are divergent and therefore the result seems ambiguous. However, we have the good news that the ambiguity have no effect on VMM. After a lengthy calculation, such as Wick rotation^[22] and the expansion of the result to order $|\mathbf{p}|, |\mathbf{p}'|, |\mathbf{q}|$, we write Γ^i and $\delta\Gamma^i$ as $\bar{u}(C_1\gamma^i + C_2i\epsilon^{ij}q^j\sigma_3/2)u$ in nonrelativistic limit, where $\epsilon^{12} = -\epsilon^{21} = 1$, $\epsilon^{11} = \epsilon^{22} = 0$, C_1 and C_2 depend on Γ^μ , $\delta\Gamma_1^i$ and $\delta\Gamma_2^i$. For all the cases, C_1 is divergent while C_2 is finite. Together with the tree diagram and counterterm, $(1+\delta_1+C_1(\Gamma^i)+C_1(\delta\Gamma_1^i)+$

$C_1(\delta\Gamma_2^i))\bar{u}\gamma^i u$ should be fixed to match renormalization conditions. Comparing with the Born approximation for scattering from a potential of carrier nearly $\mathbf{p}, \mathbf{q} \rightarrow 0$, we find that $1 + \delta_1 + C_1(\Gamma^i) + C_1(\delta\Gamma_1^i) + C_1(\delta\Gamma_2^i)$ is just the electric charge of carrier, in units of e . Due to this, we set the renormalization condition as $1 + \delta_1 + C_1(\Gamma^i) + C_1(\delta\Gamma_1^i) + C_1(\delta\Gamma_2^i) = 1$ at $\mathbf{p}, \mathbf{q} \rightarrow 0$. This renormalization condition corresponds with the fact that the carrier at lower energy ($\mathbf{p} = 0$) possesses unit (renormalized) charge e when scattered under external potential which varies very slowly.

For finite term C_2 , we have

$$C_2(\Gamma^i) = \frac{e^2}{4\epsilon m}, \quad C_2(\delta\Gamma_1^i) = -\frac{\lambda_1}{4\pi v}. \quad (8)$$

Ignoring term proportional to $\mathbf{p} + \mathbf{p}'$, which is the contribution of the operator $\mathbf{p} \cdot \mathbf{A} + \mathbf{A} \cdot \mathbf{p}$ in the standard kinetic energy term of nonrelativistic quantum mechanics, we rewrite $\bar{u}\gamma^i u$ term as

$$\bar{u}(p')\gamma^i u(p) \rightarrow \frac{-iv\epsilon^{ij}q^j}{m}\bar{u}\frac{\sigma^3}{2}u. \quad (9)$$

We obtain, then,

$$i\mathcal{M} = -i2m\xi^\dagger \frac{\sigma_3}{2}\xi \frac{ev\beta}{m}(1 - \frac{e^2}{4\epsilon v} + \frac{m}{4\pi v^2}(\lambda_1 + \lambda_2))B^3, \quad (10)$$

where $B^3 = -i(q^1 A_{cl}^2 - q^2 A_{cl}^1)$ is magnetic field perpendicular to graphene, $\xi = (1, 0)^T$ is two-component spinor and $\xi^\dagger \frac{\sigma_3}{2} \xi = 1/2 \equiv s_3$ indicates that electron pseudo-spin is 1/2.

We interpret $\mathcal{M}$ as the Born approximation to the scattering of the electron from a potential. The potential is just that of a magnetic moment interaction, $V(\mathbf{x}) = -\mu_e^3(\mathbf{K})B^3$, where

$$\mu_e^3(\mathbf{K}) = \frac{ev\beta}{m}(1 - \frac{e^2}{4\epsilon v} + \frac{m}{4\pi v^2}(\lambda_1 + \lambda_2))s_3 \quad (11)$$

is the carrier VMM parallel to B^3 at $\mathbf{K}$ valley. For the hole, we get the same value with a necessary minus sign. Similarly, for carrier at $-\mathbf{K}$ valley, VMM is also the same with a minus sign. Such phenomenon is known as the broken inversion symmetry in Ref. [9].

By recovering $\hbar$, the leading term of VMM is $e\hbar v\beta/m$, which is also obtained by ref. [9]. However, besides the leading term, there are also other contributions to VMM. The relative contribution to VMM are

$$-\frac{e^2}{4\epsilon\hbar v} - \frac{mV_s}{4\pi\hbar^2 v^2} = \alpha(-\frac{1}{4} + \frac{1.55\epsilon m a}{4\pi\hbar v}), \quad (12)$$

where $\alpha = e^2/(\epsilon\hbar v) \approx 0.73$ when $\epsilon = 3$. Substituting $a = 2.46\text{\AA}$, $v \approx 10^{-8}\text{cm/s}$ into Eq. (12), we find the relative modifications to VMM due to vertex correction and four-fermion interactions are about -18% and 3% respectively if we choose $m = 0.26eV$.

It looks strange that it is not V_d but V_s which contributes to VMM. Such behavior stems from the definition of χ field. From the definition of φ field and

χ field V_d only relates to interaction between carriers in different valley with the same pseudo-spin so that it does not contribute to VMM. On the contrary, V_s relates to interaction between carriers in different valley with the different pseudo-spin. Therefore, only V_s contributes to VMM.

5 Discussions

In this paper we have discussed the carrier interactions. The study reveals that besides the well known Coulomb repulsion between carriers, there are four-fermion interactions between carriers in different valleys. Since the interactions are short-range and contacting ones, they depend on the atom collocation detail. Therefore, the four-fermion interactions are type dependent. Our study shows that one of the four-fermion interactions attracts carriers in different valleys, which we believe to be helpful in understanding the unusual superconduction effect in graphene.

We also compute VMM from the tree level diagram, the vertex correction and the four-fermion interactions respectively. The contribution from the tree level diagram agrees with the result obtained in ref. [9]. The other two contributions counteract each other and therefore the total contribution to VMM is about -15% if we choose $m = 0.26\text{eV}$ and $\varepsilon = 3$.

The very high accurate measurement of spin magnetic moment is very important, both from theoretical viewpoint and from practical one. Similarly, our result on VMM is also significant to valleytronics in graphene, especially to the future apparatus design based on valleytronics. Our study also points out that, in close analogy to the Zeeman split, the contribution to VMM induced by V_s is inherent, since it is independent on the energy gap m . In other words, to measure the magnetic moment induced by V_s , we may choose the substrate freely, although different substrate may generate different energy gap and different effective permittivity.

From Eq. (12), α plays the same role as the fine structure constant in QED, $\alpha_e = \frac{e^2}{\hbar c} \approx 1/137$. However, because α is about 100 times larger than α_e , it is hard to state that we mimic QED by carrier interaction in graphene. Meanwhile, when we deal with problems dominated by quantum chromodynamics(QCD), especially in heavy quarkonium, such as $c\bar{c}$ system and $b\bar{b}$ system, we always take $\alpha_s = \frac{g_s^2}{\hbar c}$, where g_s is the QCD coupling, as the estimate of the effectiveness of perturbational expansion. (In many cases when we deal with such problem we take an approach very similar to QED, up to an unimportant color factor.) At energy scale 740MeV , $\alpha_s(740\text{MeV}) \approx 0.73 \approx \alpha$ [22]. Noticing that the energy scale is close to the soft scale of $c\bar{c}$ and $b\bar{b}$ systems [23], the dynamics of which is depicted by nonrelativistic QCD, we conclude that we can mimic the heavy quarkonium system by carrier in-

teractions in graphene. Therefore, the study on the heavy-quarkonium system can also be carried out in graphene.

This work is supported by the Cultivation Fund of the Key Scientific and Technical Innovation Project-Ministry of Education of China (No. 708082).

References

- [1] K.S. Novoselov, *et al.*, Science, **306**, 669(2004); K.S. Novoselov *et al.*, Nature (London) **438**, 197 (2005); Y. Zhang *et al.*, Nature (London) **438**, 201(2005).
- [2] See, for instance, A.K. Geim and K.S. Novoselov, Nature Mater. **6**, 183 (2007); M.I. Katsnelson, Mater. Today **10**, Issue 1&2, 20 (2007); M.I. Katsnelson and K.S. Novoselov, cond-mat/0703374; A. Kashuba, arXiv:0802.2261; K. Shizuya, Phys.Rev. **B75**, 245417; F. Guinea *et al*, arXiv:0803.1958.
- [3] D.Q. Liu and S.L. Zhang J. Phys.: Condens. Matter **20**, 175222 (2008); S.A. Mikhailov, K. Ziegler, J. Phys.: Condens. Matter **20**, 384204 (2008)
- [4] V.P. Gusynin, S.G. Sharapov and J.P. Carbotte, Phys. Rev. **B75**, 165407 (2007); V.P. Gusynin, S.G. Sharapov and J.P. Carbotte, J. Phys.: Condens. Matter **19**, 026222 (2007).
- [5] V.P. Gusynin and S.G. Sharapov and J.P. Carbotte, Int.J.Mod.Phys. **B21**, 4611 (2007).
- [6] P. Recher *et al*, Phys. Rev. **B76**, 235404 (2007).
- [7] S.V. Morozov *et al.*, Phys.Rev.Lett. **97**, 016801 (2006); A.F. Morpurgo and F. Guinea, Phys. Rev. Lett. **97**, 196804 (2006).
- [8] D. Xiao, J. Shi and Q. Niu, Phys.Rev.Lett. **95**, 137204 (2005).
- [9] D. Xiao, W. Yao and Q. Niu, Phys.Rev.Lett. **99**, 236809 (2007).
- [10] A. Rycerz, J. Tworzydło and C.W.J. Beenakker, Nature Phys. **3**, 172 (2007).
- [11] D.V. Bulaev, B. Trauzettel and D. Loss, Phys.Rev. **B77**, 235301 (2008).
- [12] P.R. Wallace, Phys. Rev. **71**, 622 (1947).
- [13] R. Roldán, M.P. López-Sancho and F. Guinea, Phys. Rev. **B77**, 115410 (2008).
- [14] C. Zhang, L. Chen and Z. Ma, Phys.Rev. **B77**, 241402 (2008).
- [15] B. Uchoa and CastroNeto, A.H., Phys.Rev.Lett. **98**, 146801 (2007).
- [16] G. Giovannetti *et al* Phys. Rev. **B76**, 073103 (2007).
- [17] S.Y. Zhou, *et al*, Nature Mater. **6**, 770 2007; W. Yao, S.A. Yang, and Q. Niu, Phys.Rev.Lett. **102**, 096801 (2009).

- [18] T. Ohta, A. Bostwick, T. Seyller, K. Horn and E. Rotenberg, *Science* **313**, 951 (2006)
- [19] S.Y. Zhou, *et al*, *Nature Mater.* **7**, 259 (2008)
- [20] C.K. Xu, *Phys.Rev.* **B78**, 054432 (2008).
- [21] J. González, F. Guinea and M.A.H. Vozmediano, *Nucl.Phys.* **B424**, 595 (1994).
- [22] D. Liu, *Comm.Theor.Phys.* **V46**, 1027 (2006); Y. Koide, hep-ph/9410270.
- [23] N. Brambilla, arXiv:hep-ph/0702105, (2007); D. Liu, *Chin.Phys.* **16**, 962 (2007).